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Dual P-Channel 30 V (D-S) MOSFET

Marking code: DO

Top View

PRODUCT SUMMARY									
V _{DS} (V)	-30								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -10 \text{ V}$	0.065								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -6 \text{ V}$	0.080								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.100								
Q _g typ. (nC)	4.1								
I _D (A) ^a	-4.5								
Configuration	Dual								

Bottom View

FEATURES

- TrenchFET® Gen III power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Low on-resistance
- 100 % R_g tested

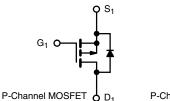
 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

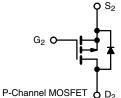


ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Smart phones, tablet PCs, mobile computing:
 - Battery switches
 - Load switches
 - Power management
 - DC/DC converters





ORDERING INFORMATION	
Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA931DJ-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unless	otherwise no	ted)				
PARAMETER		SYMBOL	LIMIT	UNIT			
Drain-source voltage	V_{DS}	-30	V				
Gate-source voltage		V_{GS}	± 20	¬			
	T _C = 25 °C		-4.5 ^a				
Continuous drain surrent (T. 150 °C)	T _C = 70 °C		-4.5 ^a				
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	-4.3 b, c				
	T _A = 70 °C		-3.4 ^{b, c}	Α			
Pulsed drain current (t = 300 μs)		I _{DM}	-28				
On all a constant of all all all and a constant	T _C = 25 °C	ı	-4.5 ^a				
Continuous source-drain diode current	T _A = 25 °C	I _S	-1.6 ^{b, c}				
	T _C = 25 °C		7.8				
Mandan and a sure distribution	T _C = 70 °C	P_{D}	5	1			
Maximum power dissipation	T _A = 25 °C		1.9 ^{b, c}	W			
	T _A = 70 °C		1.2 ^{b, c}				
Operating junction and storage temperature rai	T _J , T _{stg}	-55 to +150	°C				
Soldering recommendations (peak temperature		260	1				

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	52	65	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	12.5	16	C/VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 110 °C/W



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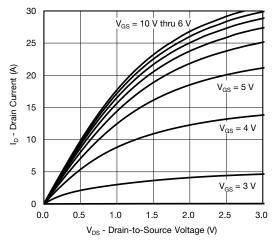
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	-24	-	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	3.4	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1.2	-	-2.2	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zono de la collega de la conseila		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10	-	-	Α
	, ,	$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A}$	-	0.052	0.065	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -6 \text{ V}, I_D = -2 \text{ A}$	-	0.063	0.080	Ω
		V _{GS} = -4.5 V, I _D = -2 A	-	0.077	0.100	
Forward transconductance a	9fs	$V_{DS} = -15 \text{ V}, I_{D} = -3 \text{ A}$	-	8	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	445	-	pF
Output capacitance	Coss	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	55	-	
Reverse transfer capacitance	C _{rss}		-	45	-	
Tatal sata abauma	0	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -4 \text{ A}$	-	8.5	13	nC
Total gate charge	Qg		-	4.1	6.2	
Gate-source charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4 \text{ A}$	-	1.2	-	
Gate-drain charge	Q _{gd}		-	1.5	-	
Gate resistance	R_{g}	f = 1 MHz	1.1	5.5	11	Ω
Turn-on delay time	t _{d(on)}		-	23	45	
Rise time	t _r	V_{DD} = -15 V, R_L = 5 Ω	-	18	35	ns
Turn-off delay time	t _{d(off)}	$I_D \cong -3 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	17	35	
Fall time	t _f		-	5	10	
Turn-on delay time	t _{d(on)}		-	8	15	
Rise time	t _r	$V_{DD} = -15 \text{ V}, R_1 = 5 \Omega$	-	5	10	
Turn-off delay time	t _{d(off)}	$I_D \cong -3 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	20	40	
Fall time	t _f		-	5	10	
Drain-Source Body Diode Characterist	ics					
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	-4.5	^
Pulse diode forward current	I _{SM}		-	-	-15	Α
Body diode voltage	V _{SD}	I _S = -3 A, V _{GS} = 0 V	-	-0.9	-1.2	V
Body diode reverse recovery time	t _{rr}		-	15	30	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = -3 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	8	20	nC
Reverse recovery fall time	ta	$T_{\rm J} = 25 ^{\circ}{\rm C}$		10	-	
Reverse recovery rise time	t _b		-	5	-	ns

Notes

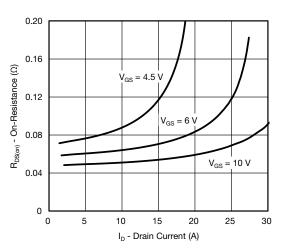
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

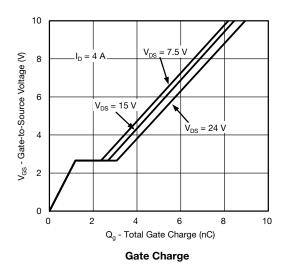


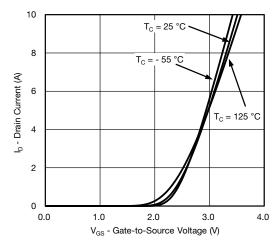


Output Characteristics

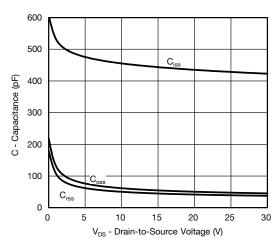


On-Resistance vs. Drain Current and Gate Voltage

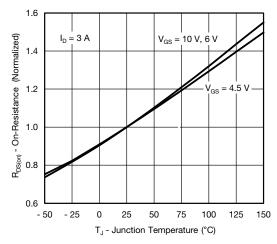




Transfer Characteristics

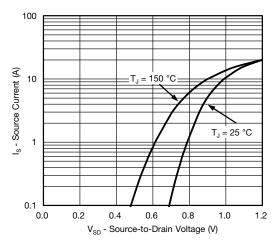


Capacitance

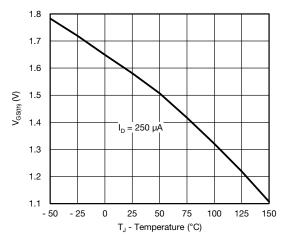


On-Resistance vs. Junction Temperature

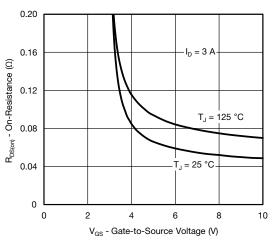




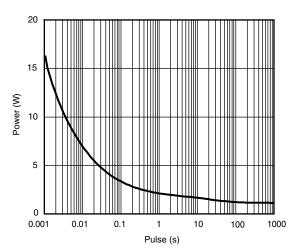
Soure-Drain Diode Forward Voltage



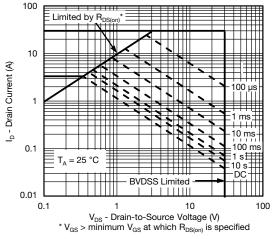
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

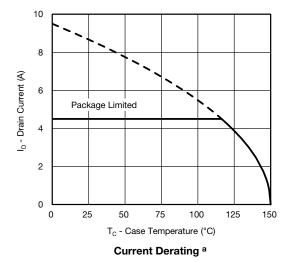


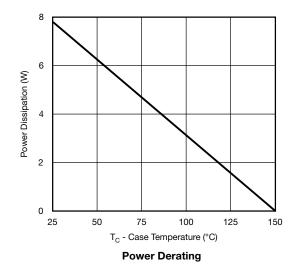
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient



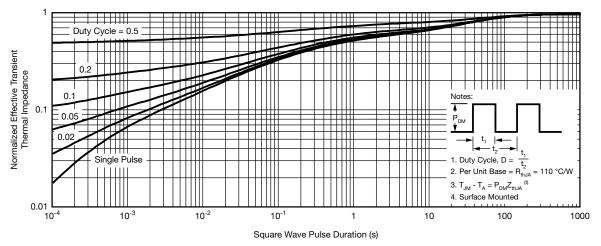




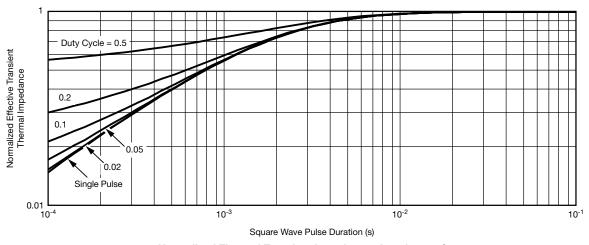
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62859.





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PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP		
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP						•	•	
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

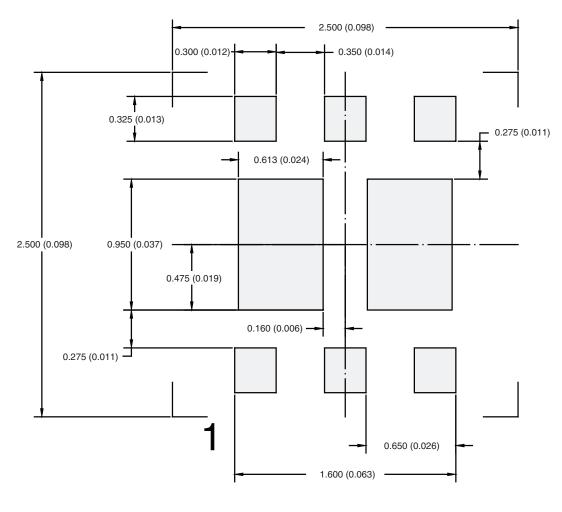
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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